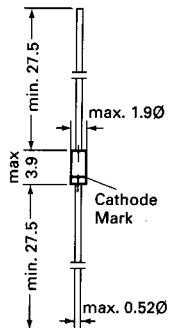


1N 4148 SILICON EPITAXIAL PLANAR DIODE

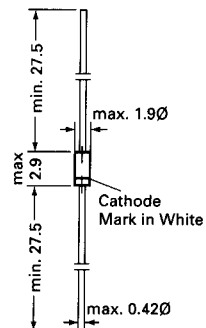
Silicon Epitaxial Planar Diode

fast switching diode.

This diode is also available in MiniMELF case with the type designation LL4148.



Glass case JEDEC DO-35



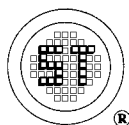
Glass case JEDEC DO-34

Dimensions in mm

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

	Symbol	Value	Unit
Reverse Voltage	V_R	75	V
Peak Reverse Voltage	V_{RM}	100	V
Rectified Current (Average) Half Wave Rectification with Resist. Load at $T_{amb} = 25\text{ }^\circ\text{C}$ and $f \geq 50\text{ Hz}$	I_o	150 ¹⁾	mA
Surge Forward Current at $t < 1\text{ s}$ and $T_j = 25\text{ }^\circ\text{C}$	I_{FSM}	500	mA
Power Dissipation at $T_{amb} = 25\text{ }^\circ\text{C}$	P_{tot}	500 ¹⁾	mW
Junction Temperature	T_j	200	$^\circ\text{C}$
Storage Temperature Range	T_s	-65 to + 200	$^\circ\text{C}$

¹⁾ Valid provided that leads at a distance of 8 mm from case are kept at ambient temperature



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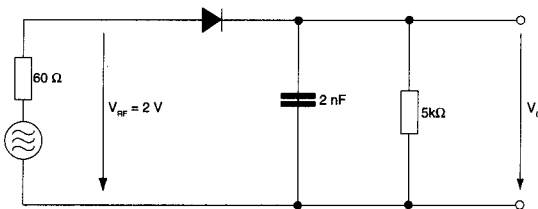
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SILICON EPITAXIAL PLANAR DIODE

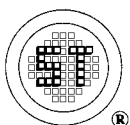
Characteristics at $T_j = 25\text{ }^\circ\text{C}$

	Symbol	Min.	Typ.	Max.	Unit
Forward Voltage at $I_F = 10\text{ mA}$	V_F	-	-	1	V
Leakage Current at $V_R = 20\text{ V}$ at $V_R = 75\text{ V}$ at $V_R = 20\text{ V}, T_j = 150\text{ }^\circ\text{C}$	I_{R1} I_{R2} I_{R3}	- - -	- - -	25 5 50	nA μA μA
Reverse Breakdown Voltage tested with $100\text{ }\mu\text{A}$ Pulses	$V_{(BR)R}$	100	-	-	V
Capacitance at $V_F = V_R = 0$	C_{tot}	-	-	4	pF
Voltage Rise when Switching ON tested with 50 mA Forward Pulses $t_p = 0.1\text{ s}$, Rise Time $< 30\text{ ns}$, $f_p = 5\text{ to }100\text{ kHz}$	V_{fr}	-	-	2.5	V
Reverse Recovery Time from $I_F = 10\text{ mA}$ to $I_R = 1\text{ mA}$, $V_R = 6\text{ V}$, $R_L = 100\text{ }\Omega$,	t_{rr}	-	-	4	ns
Thermal Resistance Junction to Ambient Air	R_{thA}	-	-	0.35 ¹⁾	K/mW
Rectification Efficiency at $f = 100\text{ MHz}$, $V_{RF} = 2\text{ V}$	η_V	0.45	-	-	-

¹⁾ Valid provided that leads at a distance of 8 mm from case are kept at ambient temperature



Rectification Efficiency Measurement Circuit

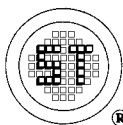
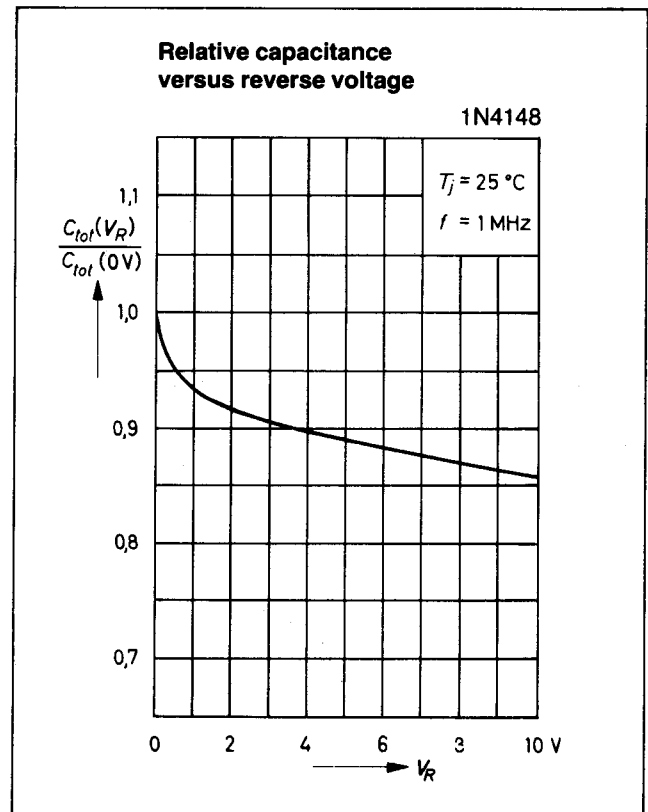
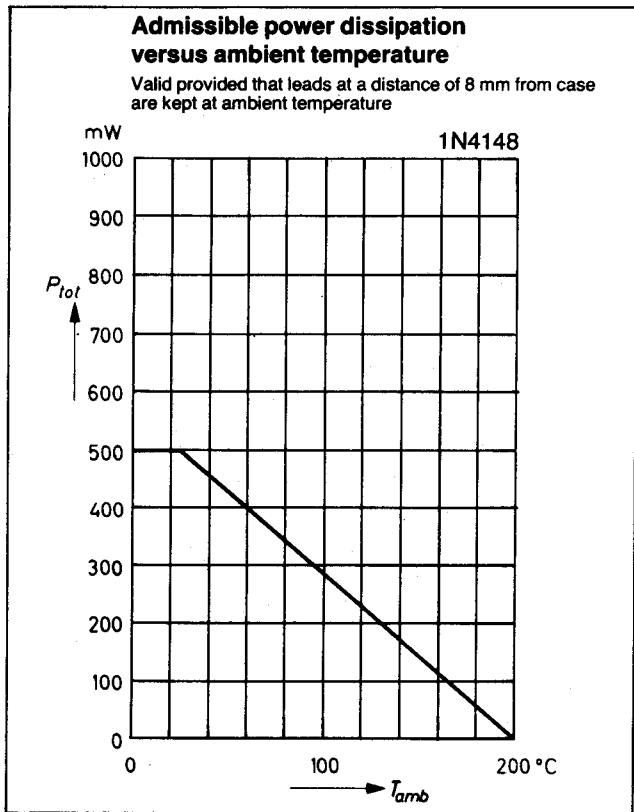
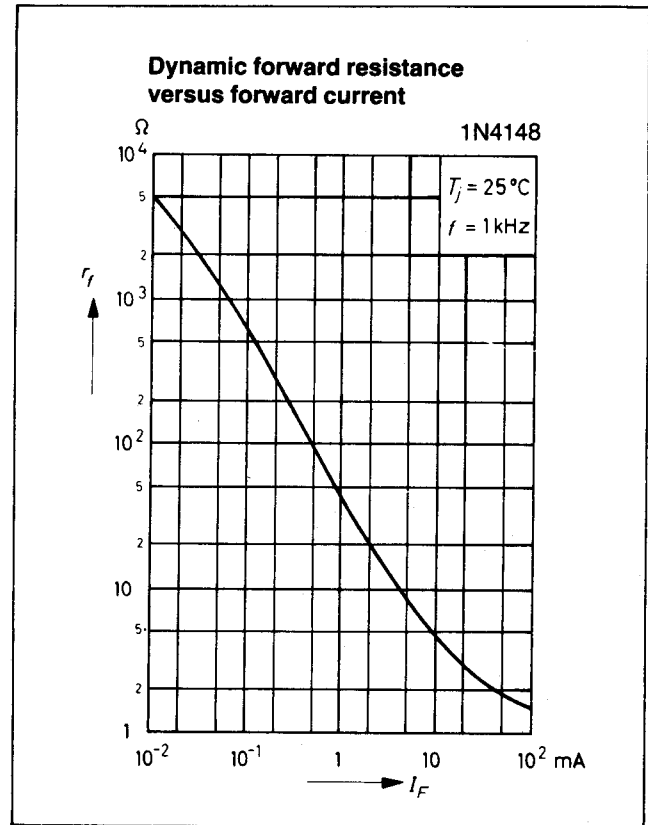
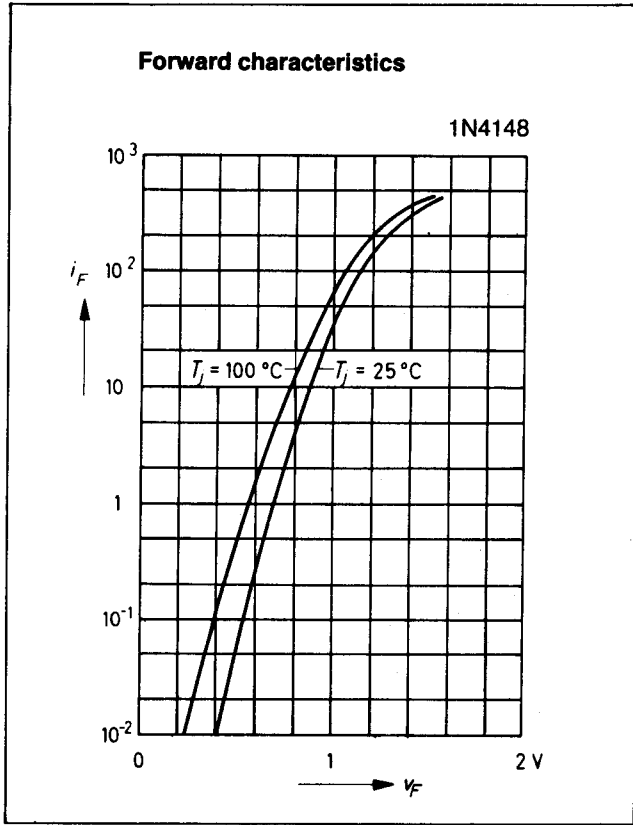


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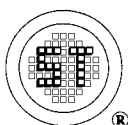
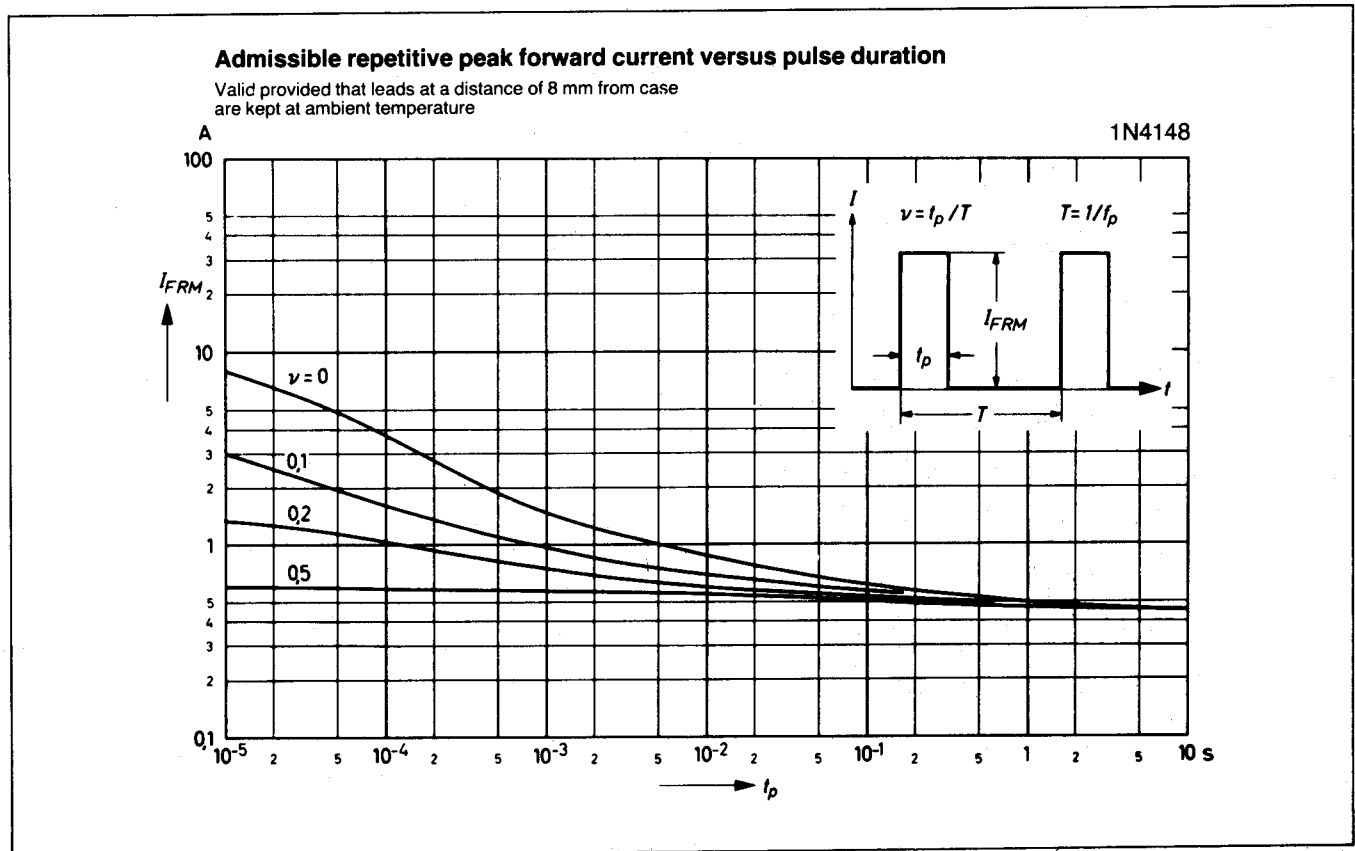
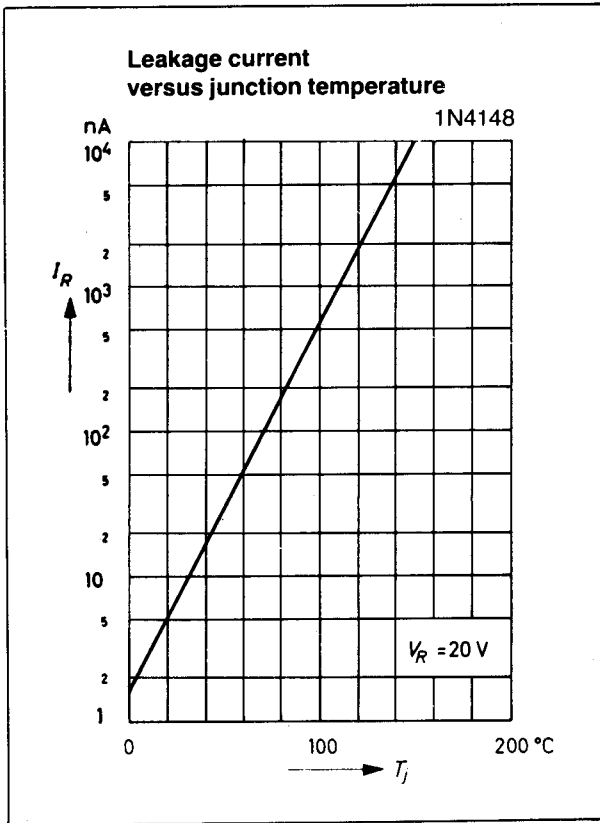
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